



2SB893 (3CG893)

硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途：用于电源，继电器驱动，灯驱动，闪光驱动。

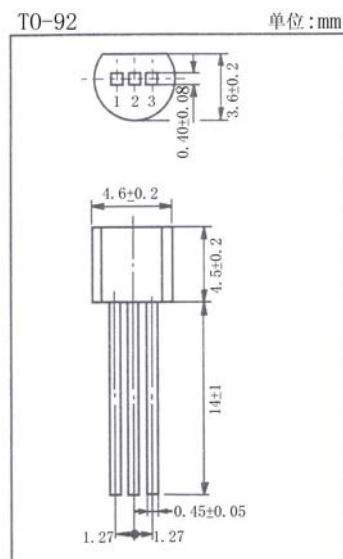
Purpose: Power supplies, relay drivers, lamp drivers, strobes.

特点：饱和压降低，电流容量大，安全工作区宽。

Features: Low saturation voltage, large current capacity and wide ASO.

极限参数/Absolute maximum ratings (Ta=25°C)

参数符 Symbol	数值 Rating	单位 Unit
V <sub>CB0</sub>	-20	V
V <sub>CE0</sub>	-10	V
V <sub>EB0</sub>	-7.0	V
I <sub>C</sub>	-2.5	A
I <sub>C(Pulse)</sub>	-5.0	A
P <sub>C</sub>	750	mW
T <sub>j</sub>	150	°C
T <sub>stg</sub>	-55~150	°C



引脚: 1. E 2. C 3. B

电性能参数/Electrical characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V <sub>CB0</sub>	I <sub>C</sub> =-10 μA	I <sub>E</sub> =0	-20			V
V <sub>CE0</sub>	I <sub>C</sub> =-1.0mA	R <sub>BE</sub> =∞	-10			V
V <sub>EB0</sub>	I <sub>E</sub> =-10 μA	I <sub>C</sub> =0	-7.0			V
I <sub>CB0</sub>	V <sub>CB</sub> =-20V	I <sub>E</sub> =0			-1.0	μA
I <sub>EB0</sub>	V <sub>EB</sub> =-4.0V	I <sub>C</sub> =0			-1.0	μA
h <sub>FE(1)</sub>	V <sub>CE</sub> =-2.0V	I <sub>C</sub> =-500mA	100		560	
*h <sub>FE(2)</sub>	V <sub>CE</sub> =-2.0V	I <sub>C</sub> =-3A	70			
V <sub>CE(sat)</sub>	I <sub>C</sub> =-1.5A	I <sub>B</sub> =-150mA		-0.25	-0.45	V
f <sub>T</sub>	V <sub>CE</sub> =-10V	I <sub>C</sub> =-50mA		250		MHz
C <sub>ob</sub>	V <sub>CB</sub> =-10V	f=1.0MHz		70		pF

\*:pulse test/脉冲测试。

h<sub>FE(1)</sub> 分档/h<sub>FE(1)</sub> classifications: E: 100~200 F: 160~320 G: 280~560

